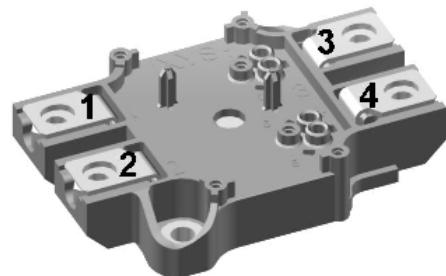


Standard Rectifier Module

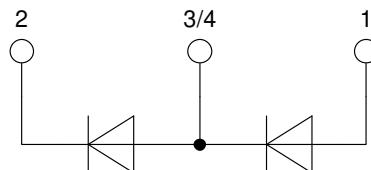
 $V_{RRM} = 2 \times 1600 \text{ V}$
 $I_{FAV} = 200 \text{ A}$
 $V_F = 1.06 \text{ V}$

Phase leg

Part number

MDMA200P1600SA


Backside: isolated

 E72873


Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: SimBus A

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Gate: Spring contacts for solder-free PCB-mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

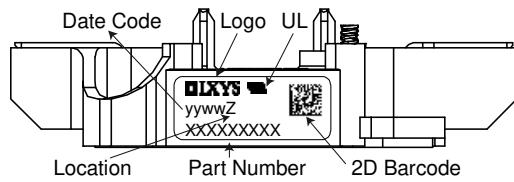
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_R	reverse current	$V_R = 1600 \text{ V}$ $V_R = 1600 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		200 15	μA mA
V_F	forward voltage drop	$I_F = 200 \text{ A}$ $I_F = 400 \text{ A}$ $I_F = 200 \text{ A}$ $I_F = 400 \text{ A}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.13 1.33 1.06 1.32	V V
I_{FAV}	average forward current	$T_C = 110^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ C$		200	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.76 1.4	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.15	K/W
R_{thCH}	thermal resistance case to heatsink			0.08		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		830	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ C$ $V_R = 0 \text{ V}$		6.00 6.48 5.10 5.51	kA kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ C$ $V_R = 0 \text{ V}$		180.0 174.7 130.1 126.3	kA^2s kA^2s kA^2s kA^2s
C_J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	273		pF

Package SimBus A

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			300	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				152		g
M_D	mounting torque		3		5	Nm
M_T	terminal torque		2.5		5	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/Apb}$		terminal to backside	14.0	10.0		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800 4000			V V

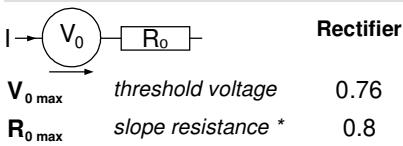

Part description

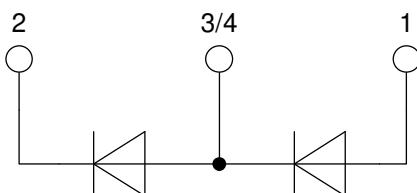
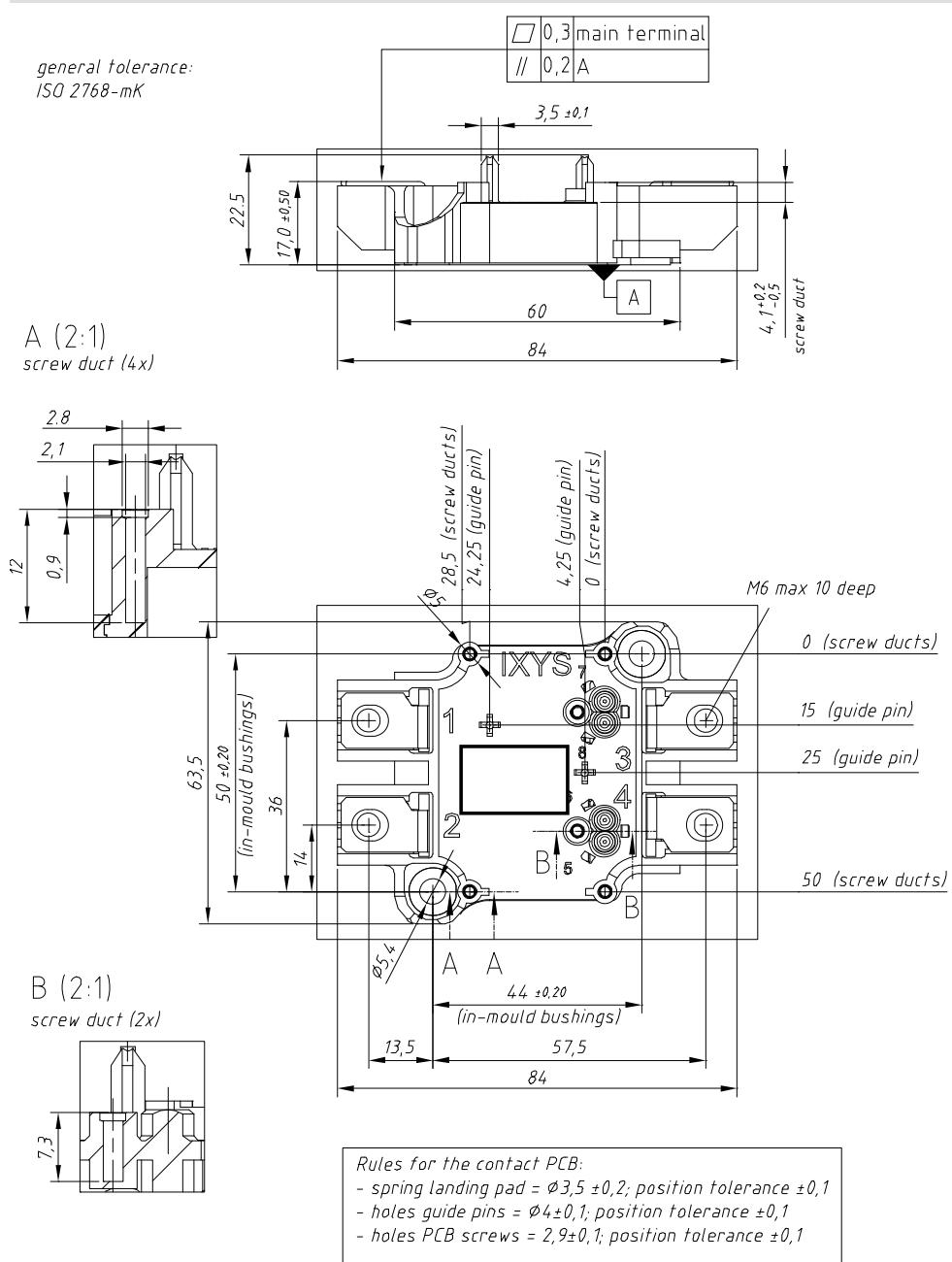
M = Module
D = Diode
M = Standard Rectifier
A = (up to 1800V)
200 = Current Rating [A]
P = Phase leg
1600 = Reverse Voltage [V]
SA = SimBus A

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA200P1600SA	MDMA200P1600SA	Blister	9	510373

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^\circ\text{C}$


Outlines SimBus A


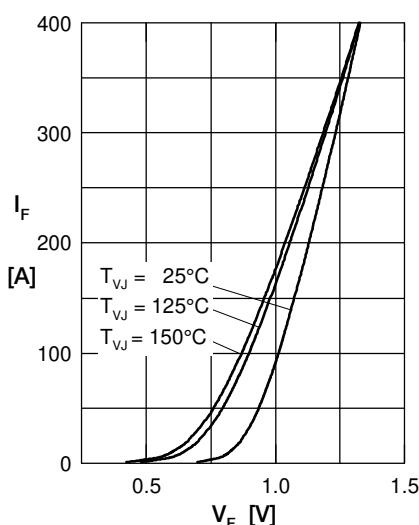
Rectifier


Fig. 1 Forward current versus voltage drop per diode

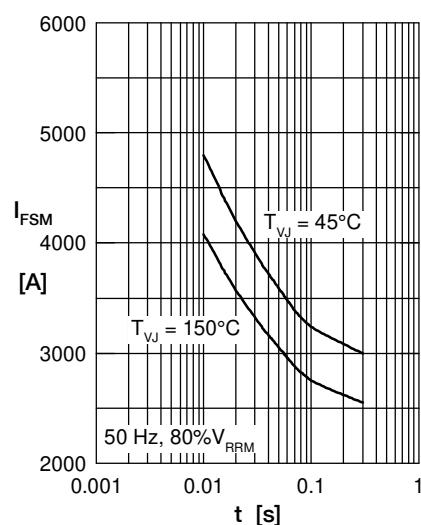


Fig. 2 Surge overload current vs. time per diode

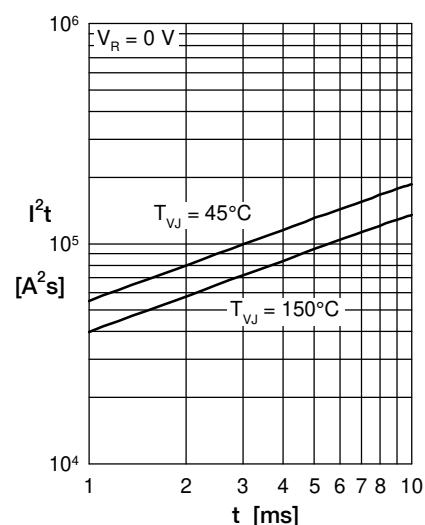


Fig. 3 I^2t versus time per diode

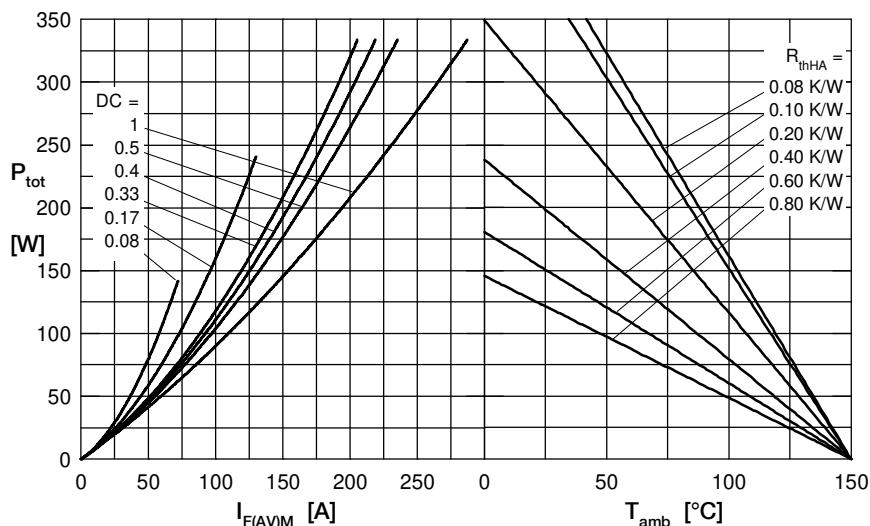


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

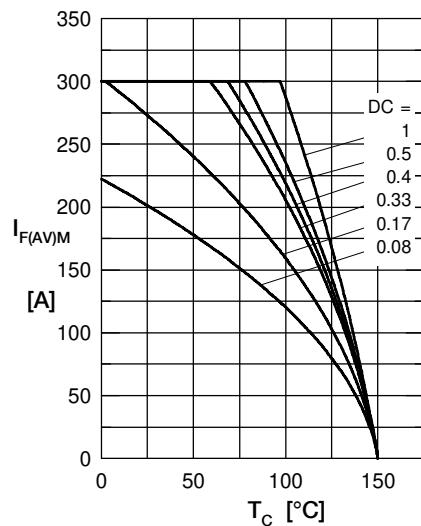


Fig. 5 Max. forward current vs. case temperature per diode

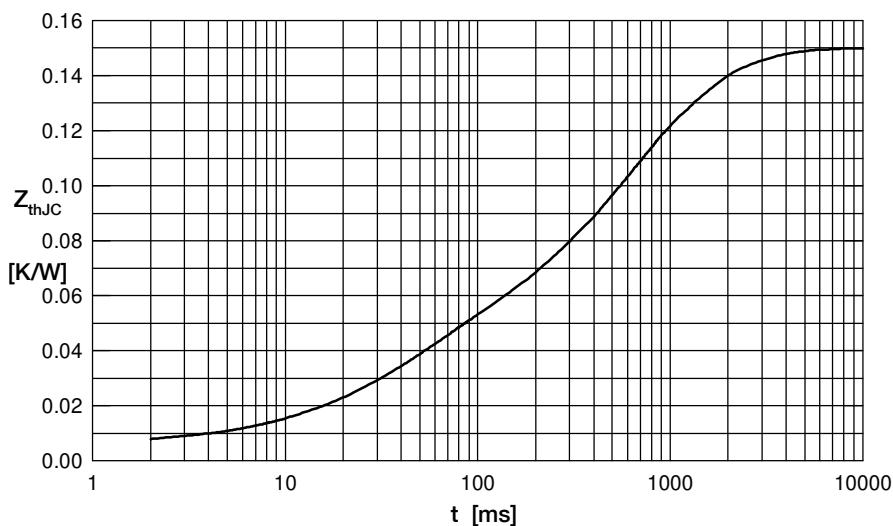


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.006	0.0005
2	0.035	0.0400
3	0.079	0.5500
4	0.030	1.5000